

**Features**

- High Surge Capability
- Types up to 600 V  $V_{RRM}$

**DO-4 Package**
**Note:**

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.


**Maximum ratings, at  $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise specified ("R" devices have leads reversed)**

Parameter	Symbol	Conditions	FR16B(R)02	FR16D(R)02	FR16G(R)02	FR16J(R)02	Unit
Repetitive peak reverse voltage	$V_{RRM}$		100	200	400	600	V
RMS reverse voltage	$V_{RMS}$		70	140	280	420	V
DC blocking voltage	$V_{DC}$		100	200	400	600	V
Continuous forward current	$I_F$	$T_C \leq 100\text{ }^\circ\text{C}$	16	16	16	16	A
Surge non-repetitive forward current, Half Sine Wave	$I_{FSM}$	$T_C = 25\text{ }^\circ\text{C}$ , $t_p = 8.3\text{ ms}$	225	225	225	225	A
Operating temperature	$T_J$		-65 to 150	-65 to 150	-65 to 150	-65 to 150	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-65 to 175	-65 to 175	-65 to 175	-65 to 175	$^\circ\text{C}$

**Electrical characteristics, at  $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	FR16B(R)02	FR16D(R)02	FR16G(R)02	FR16J(R)02	Unit
Diode forward voltage	$V_F$	$I_F = 16\text{ A}$ , $T_J = 25\text{ }^\circ\text{C}$	1.4	1.4	1.4	1.4	V
Reverse current	$I_R$	$V_R = 100\text{ V}$ , $T_J = 25\text{ }^\circ\text{C}$	25	25	25	25	$\mu\text{A}$
		$V_R = 100\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$	6	6	6	6	mA
<b>Recovery Time</b>							
Maximum reverse recovery time	$T_{RR}$	$I_F = 0.5\text{ A}$ , $I_R = 1.0\text{ A}$ , $I_{RR} = 0.25\text{ A}$	200	200	200	250	nS
<b>Thermal characteristics</b>							
Thermal resistance, junction - case	$R_{\theta JC}$		1.5	1.5	1.5	1.5	$^\circ\text{C/W}$



Figure 1-Typical Forward Characteristics

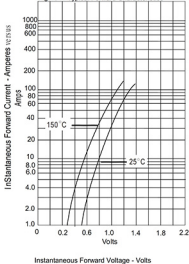


Figure 2-Forward Derating Curve

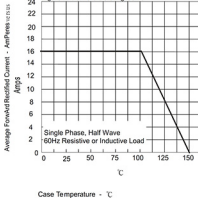


Figure 3-Peak Forward Surge Current

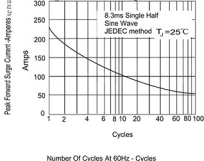


Figure 4-Typical Reverse Characteristics

